FAIRCHILD SEMICONDUCTOR®

April 2008

FDMS8670AS

N-Channel PowerTrench® SyncFET™

30V, 42A, 3.0mΩ

Features

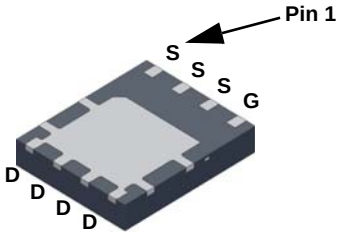
- Max $r_{DS(on)}$ = 3.0mΩ at V_{GS} = 10V, I_D = 23A
- Max $r_{DS(on)}$ = 4.7mΩ at V_{GS} = 4.5V, I_D = 18A
- Advanced Package and Silicon combination for low $r_{DS(on)}$ and high efficiency
- SyncFET Schottky Body Diode
- MSL1 robust package design
- RoHS Compliant

General Description

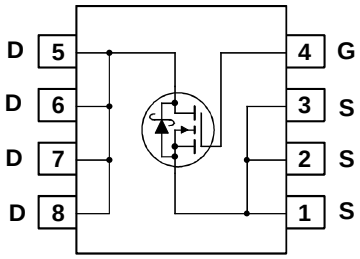
The FDMS8670AS has been designed to minimize losses in power conversion application. Advancements in both silicon and package technologies have been combined to offer the lowest $r_{DS(on)}$ while maintaining excellent switching performance. This device has the added benefit of an efficient monolithic Schottky body diode.

Applications

- Synchronous Rectifier for DC/DC Converters
- Notebook Vcore/ GPU low side switch
- Networking Point of Load low side switch
- Telecom secondary side rectification



Power 56 (Bottom view)



MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			30	V
V_{GS}	Gate to Source Voltage			±20	V
I_D	Drain Current -Continuous (Package limited)	T_C = 25°C		42	A
	-Continuous (Silicon limited)	T_C = 25°C		127	
	-Continuous	T_A = 25°C	(Note 1a)	23	
	-Pulsed			200	
E_{AS}	Single Pulse Avalanche Energy			384	mJ
P_D	Power Dissipation	T_C = 25°C		50	W
	Power Dissipation	T_A = 25°C	(Note 1a)	2.5	
T_J, T_{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.6	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS8670AS	FDMS8670AS	Power 56	13''	12mm	3000units

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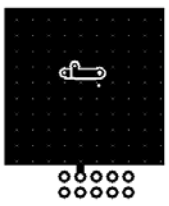
Electrical Characteristics T_J = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 1mA, V_{GS} = 0V	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 10mA, referenced to 25°C		28		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 24V, V_{GS} = 0V			500	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 1mA	1.0	1.7	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 10mA, referenced to 25°C		-5		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10V, I_D = 23A		2.4	3.0	mΩ
		V_{GS} = 4.5V, I_D = 18A		3.5	4.7	
		V_{GS} = 10V, I_D = 23A, T_J = 125°C		3.5	4.7	
g_{FS}	Forward Transconductance	V_{DD} = 10V, I_D = 23A		143		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 15V, V_{GS} = 0V, f = 1MHz		2718	3615	pF
C_{oss}	Output Capacitance			1537	2045	pF
C_{rss}	Reverse Transfer Capacitance			343	515	pF
R_g	Gate Resistance	f = 1MHz		0.9		Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 15V, I_D = 23A, V_{GS} = 10V, R_{GEN} = 6Ω		14	26	ns
t_r	Rise Time			5	10	ns
$t_{d(off)}$	Turn-Off Delay Time			32	52	ns
t_f	Fall Time			4	10	ns
Q_g	Total Gate Charge	V_{GS} = 0V to 10V; V_{DD} = 15V, I_D = 23A		39	55	nC
Q_g	Total Gate Charge	V_{GS} = 0V to 4.5V; V_{DD} = 15V, I_D = 23A		20	28	nC
Q_{gs}	Gate to Source Charge	V_{DD} = 15V, I_D = 23A		7.2		nC
Q_{gd}	Gate to Drain “Miller” Charge	V_{DD} = 15V, I_D = 23A		4.0		nC
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0V, I_S =2A (Note 3)		0.4	0.7	V
t_{rr}	Reverse Recovery Time	I_F = 23A, di/dt = 300A/μs		39	63	ns
Q_{rr}	Reverse Recovery Charge			48	77	nC

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 50°C/W when mounted on a 1 in^2 pad of 2 oz copper.

b. 125°C/W when mounted on a minimum pad of 2 oz copper.

2. Starting T_J = 25°C, L = 3mH, I_{AS} = 16A, V_{DD} = 30V, V_{GS} =10V.

3. Pulse Test: Pulse Width < 300μs, Duty cycle < 2.0%.

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Typical Characteristics T_J = 25°C unless otherwise noted

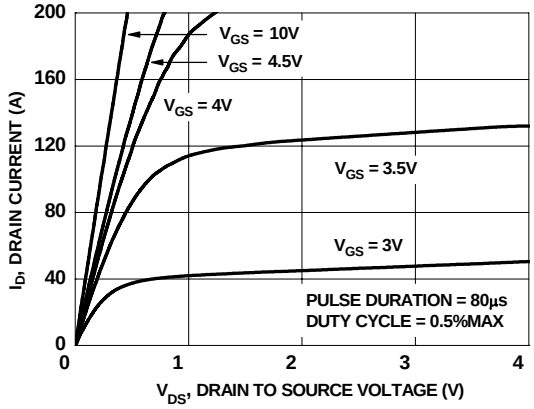


Figure 1. On-Region Characteristics

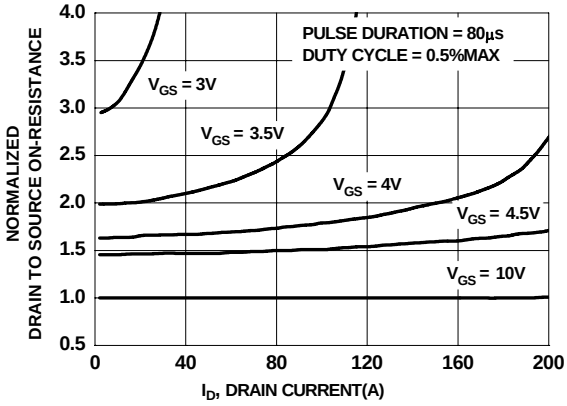


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

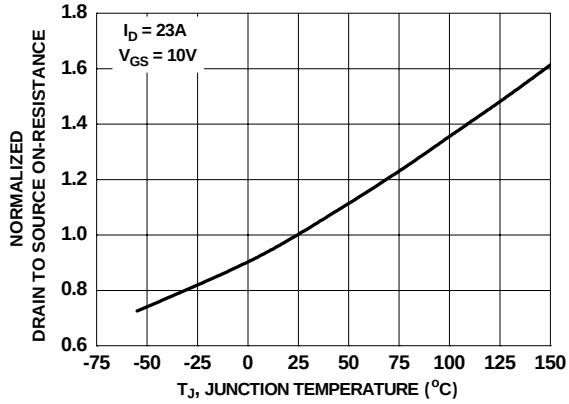


Figure 3. Normalized On-Resistance vs Junction Temperature

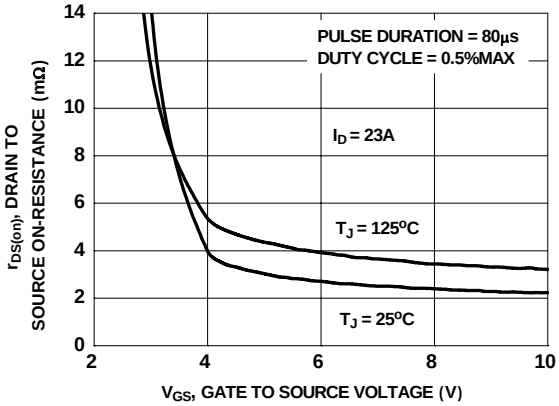


Figure 4. On-Resistance vs Gate to Source Voltage

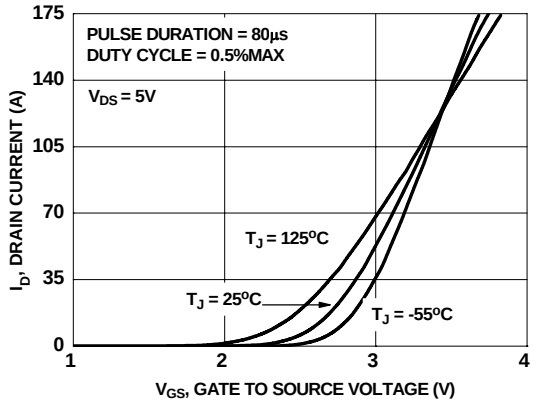


Figure 5. Transfer Characteristics

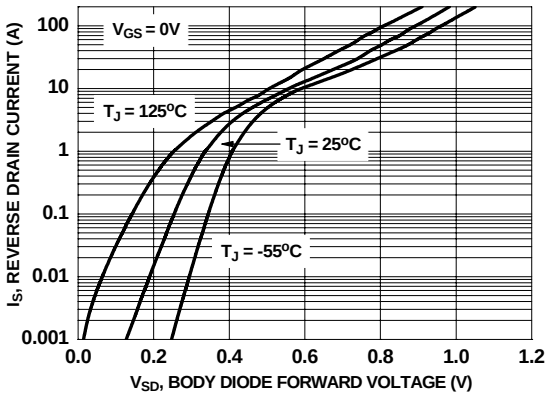


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25°C unless otherwise noted

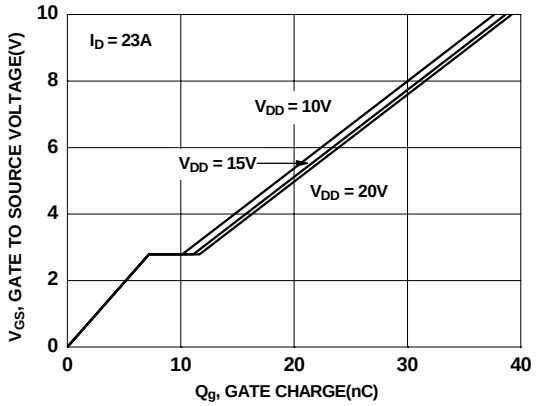


Figure 7. Gate Charge Characteristics

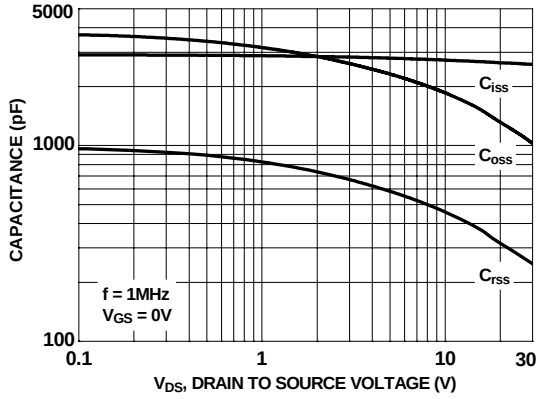


Figure 8. Capacitance vs Drain to Source Voltage

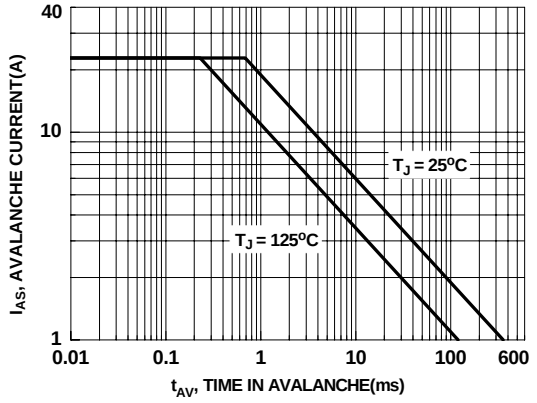


Figure 9. Unclamped Inductive Switching Capability

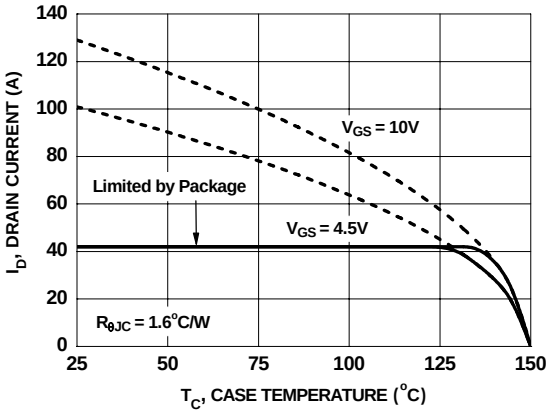


Figure 10. Maximum Continuous Drain Current vs Case Temperature

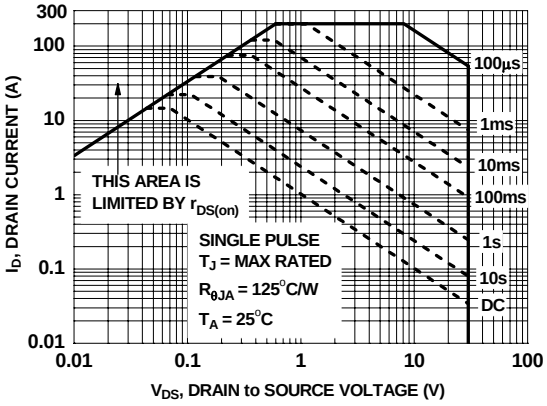


Figure 11. Forward Bias Safe Operating Area

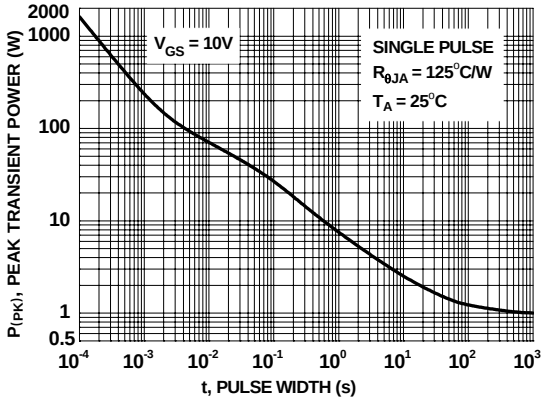


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25°C unless otherwise noted

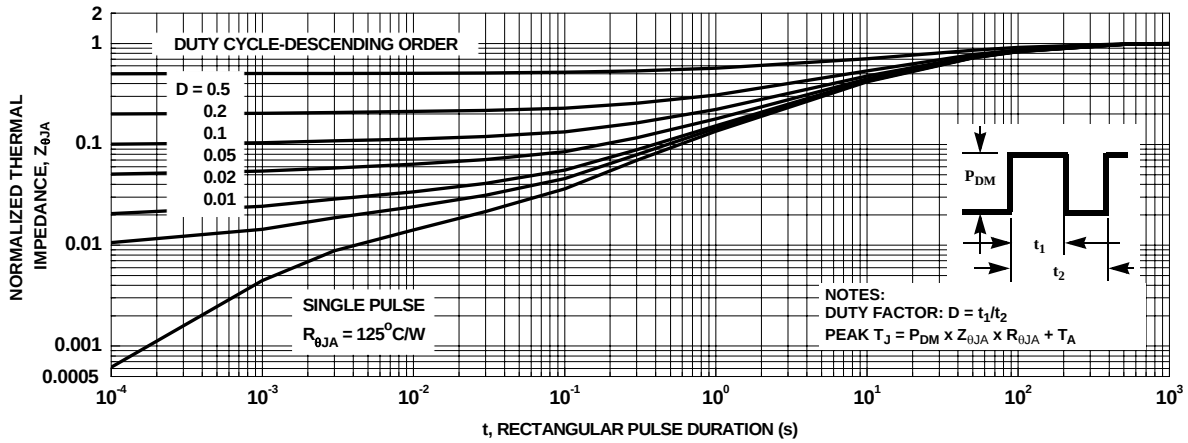


Figure 13. Transient Thermal Response Curve

Typical Characteristics (continued)

SyncFET Schottky Body Diode Characteristics

Fairchild's SyncFET process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 14 shows the reverse recovery characteristic of the FDMS8670AS.

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

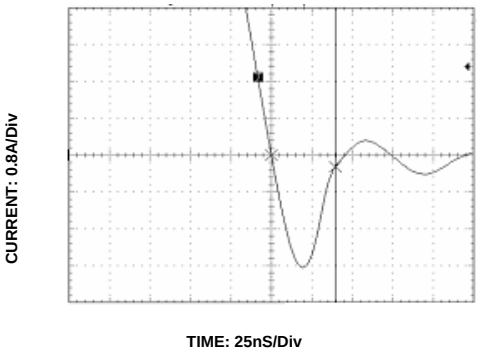


Figure 14. FDMS8670AS SyncFET Body Diode Reverse Recovery Characteristics

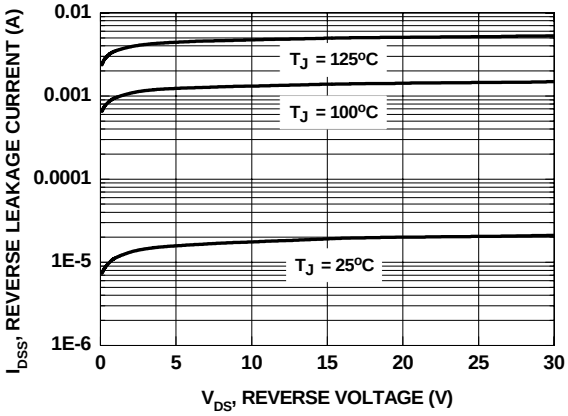
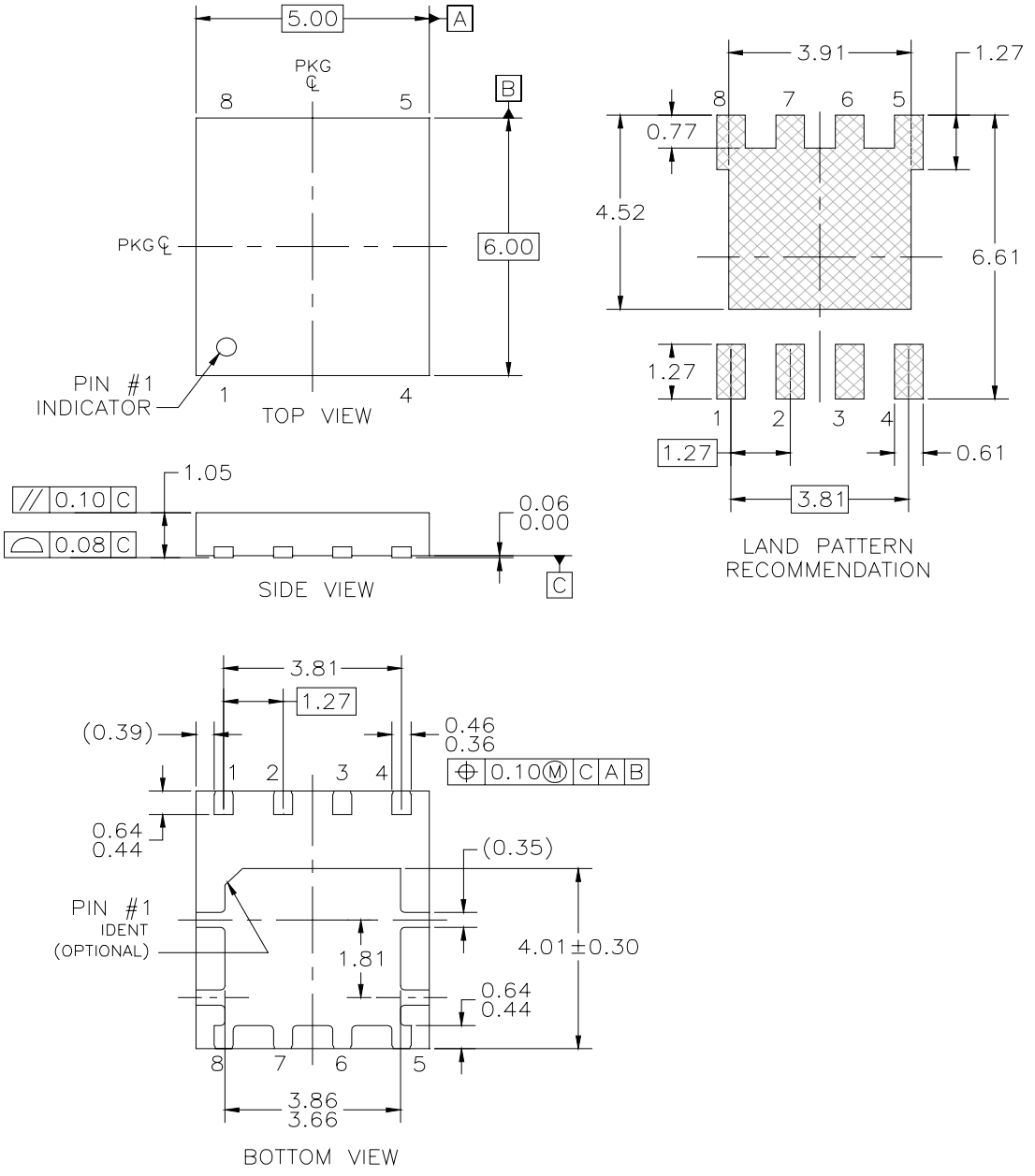


Figure 15. SyncFET Body Diode Reverse Leakage vs Drain to Source Voltage



NOTES: UNLESS OTHERWISE SPECIFIED

A) ALL DIMENSIONS ARE IN MILLIMETERS.

B) NO JEDEC REFERENCE AS OF FEBRUARY 2006

C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M 1994

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